

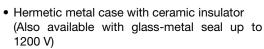
Phase Control Thyristors (Stud Version), 230 A



PRODUCT SUMMARY		
I _{T(AV)}	230 A	
V_{DRM}/V_{RRM}	400 V, 1600 V	
V_{TM}	1.55 V	
I _{GT}	150 mA	
TJ	-40 °C to 125 °C	
Package	TO-209AB (TO-93)	
Diode variation	Single SCR	

FEATURES

- Center amplifying gate
- International standard case TO-209AB (TO-93)





- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- · Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		230	A		
I _{T(AV)}	T _C	85	°C		
I _{T(RMS)}		360	A		
	50 Hz	5700	- A		
I _{TSM}	60 Hz	5970	^		
l ² t	50 Hz	163	kA ² s		
	60 Hz	149	KA-S		
V_{DRM}/V_{RRM}		400 to 1600	V		
t _q	Typical	100	μs		
T _J		-40 to 125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA				
	04	400	500					
VC CTOOC	08	800	900	20				
VS-ST230S	12	1200	1300	30				
	16	1600	1700					



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	1	190° condu	ction, half sine v	4/0//0	230	Α
at case temperature	I _{T(AV)}	160 Condu	ction, nan sine v	wave	85	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 78 °C	case temperati	ure	360	
		t = 10 ms	No voltage		5700	
Maximum peak, one-cycle	I	t = 8.3 ms	reapplied		5970	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		4800	
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	5000	
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage		163	
		t = 8.3 ms	reapplied		148	
Waxiiiluiii i tioi lusiiig		t = 10 ms	100 % V _{RRM}		115	
		t = 8.3 ms	reapplied		105	
Maximum $I^2\sqrt{t}$ for fusing	l²√t	t = 0.1 to 10) ms, no voltage	reapplied	1630	kA²√s
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.92	\ \
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		0.98	V
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum		0.88	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		0.81	11122	
Maximum on-state voltage	V_{TM}	$I_{pk} = 720 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$		1.55	V	
Maximum holding current	I _H	T. = 25 °C			600	mA
Maximum (typical) latching current	l _L	$T_J = 25$ °C, anode supply 12 V resistive load 1000 (30		1000 (300)	111/4	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs	
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0		
Typical turn-off time	t _q	$I_{TM} = 300 \text{ A, } T_J = T_J \text{ maximum, } dI_F/dt = 20 \text{ A/}\mu\text{s,}$ $V_R = 50 \text{ V, } dV/dt = 20 \text{ V/}\mu\text{s, } \text{gate } 0 \text{ V } 100 \Omega, t_p = 500 \mu\text{s}$	100	μs	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	30	mA



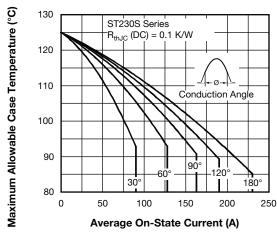
TRIGGERING						
PARAMETER	SYMBOL	-	TEGT COMPLETIONS		VALUES	
PARAMETER	STWIDGE	•	EST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	10.0		W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	3.	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms		20		V
Maximum peak negative gate voltage	- V _{GM}			5.0		
		T _J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest	180	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C		90	150	mA
		T _J = 125 °C		40	-	
		T _J = - 40 °C	value which will trigger all units 12	2.9	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	V anode to cathode applied	1.8	3.0	V
		T _J = 125 °C		1.2	-	
DC gate current not to trigger	I _{GD}	T. T. massimum	Maximum gate current/voltage not to trigger is the maximum value	10		mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J \text{ maximum}$	which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.:	25	V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	°C		
Maximum storage temperature range	T _{Stg}		-40 to 150			
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.10	K/W		
Maximum thermal resistance, case to heatsink	R _{thC-hs}	Mounting surface, smooth, flat and greased	0.04	7 r/vv		
Mounting torque + 10.0/		Non-lubricated threads	31 (275)	N·m		
Mounting torque, ± 10 %		Lubricated threads	24.5 (210)	(lbf · in)		
Approximate weight			280	g		
Case style		See dimensions - link at the end of datasheet	TO-209AB (ГО-93)		

△R _{th} JC CONDUCTION					
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS	
180°	0.016	0.012			
120°	0.019	0.020			
90°	0.025	0.027	$T_J = T_J$ maximum	K/W	
60°	0.036	0.037			
30°	0.060	0.060			

Note

The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC





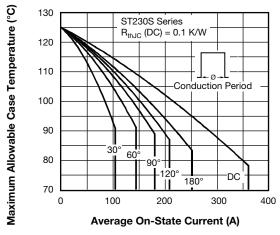


Fig. 2 - Current Ratings Characteristics

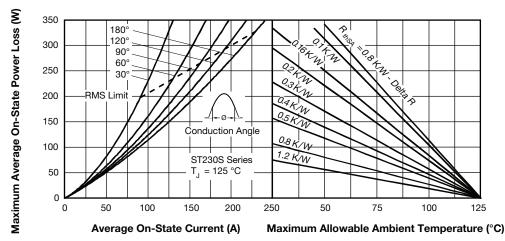


Fig. 3 - On-State Power Loss Characteristics

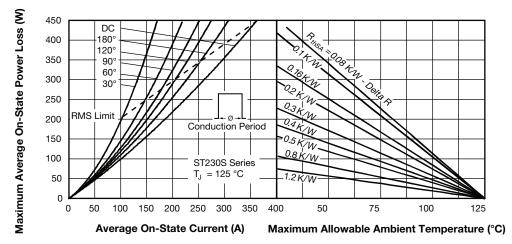


Fig. 4 - On-State Power Loss Characteristics

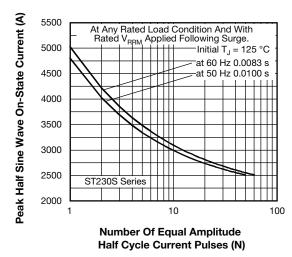


Fig. 5 - Maximum Non-Repetitive Surge Current

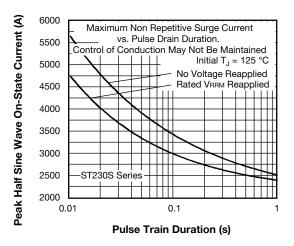


Fig. 6 - Maximum Non-Repetitive Surge Current

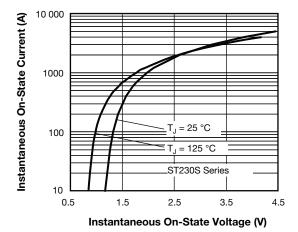


Fig. 7 - On-State Voltage Drop Characteristics

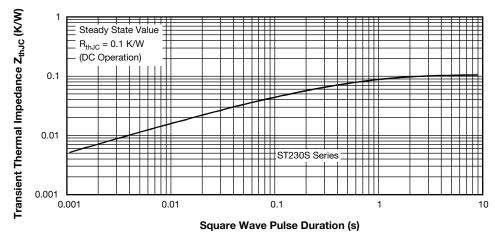


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

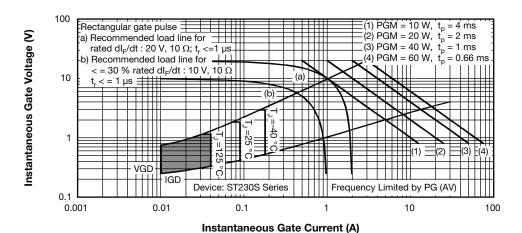
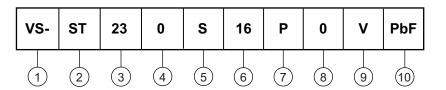


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 **Thyristor**

3 Essential part number

0 = Converter grade

S = Compression bonding stud

Voltage code x 100 = V_{RRM} (see Voltage Ratings table) 6

P = Stud base 3/4"-16UNF2A threads

0 = Eyelet terminals (gate and auxiliary cathode leads)

1 = Fast-on terminals (gate and auxiliary cathode leads)

9 • V = Glass-metal seal (only up to 1200 V)

• None = Ceramic housing (over 1200 V)

10 None = Standard production

PbF = Lead (Pb)-free

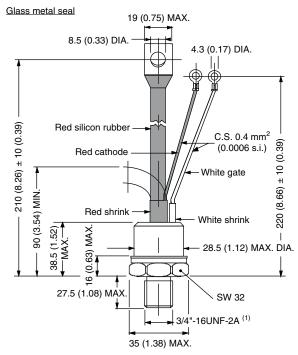
Note: For metric device M16 x 1.5 contact factory

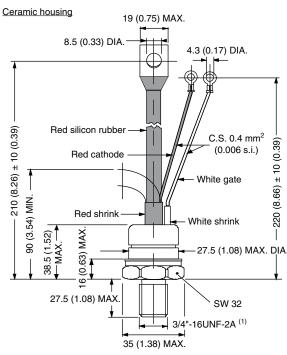
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95082

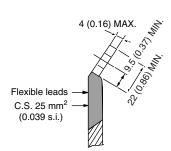


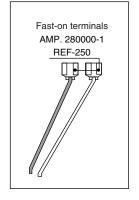
TO-209AB (TO-93)

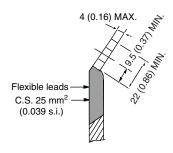
DIMENSIONS in millimeters (inches)











Note

(1) For metric device: M16 x 1.5 - length 21 (0.83) maximum



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AMEYA360 Components Supply Platform

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